

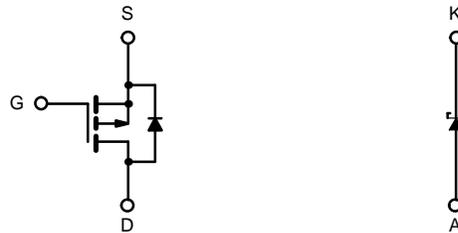
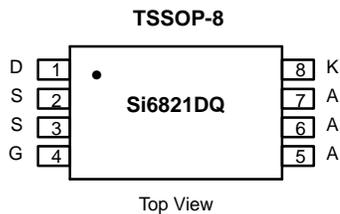


P-Channel, Reduced Q_g , MOSFET with Schottky Diode

MOSFET PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-20	0.190 @ $V_{GS} = -4.5$ V	± 1.7
	0.280 @ $V_{GS} = -3.0$ V	± 1.3

SCHOTTKY PRODUCT SUMMARY		
V_{KA} (V)	V_F (V) Diode Forward Voltage	I_F (A)
20	0.5 V @ 1 A	1.5

LITTLE FOOT Plus™



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage (MOSFET)	V_{DS}	-20	V	
Reverse Voltage (Schottky)	V_{KA}	20		
Gate-Source Voltage (MOSFET)	V_{GS}	± 12		
Continuous Drain Current ($T_J = 150^\circ\text{C}$) (MOSFET) ^{a, b}	I_D	$T_A = 25^\circ\text{C}$	± 1.7	A
		$T_A = 70^\circ\text{C}$	± 1.3	
Pulsed Drain Current (MOSFET)	I_{DM}	± 8		
Continuous Source Current (MOSFET Diode Conduction) ^{a, b}	I_S	-1.0		
Average Forward Current (Schottky)	I_F	1.5		
Pulsed Forward Current (Schottky)	I_{FM}	30		
Maximum Power Dissipation (MOSFET) ^{a, b}	P_D	$T_A = 25^\circ\text{C}$	1.2	W
		$T_A = 70^\circ\text{C}$	0.76	
Maximum Power Dissipation (Schottky) ^{a, b}	P_D	$T_A = 25^\circ\text{C}$	1.0	
		$T_A = 70^\circ\text{C}$	0.64	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter	Device	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ($t \leq 10$ sec) ^a	MOSFET	R_{thJA}	115	105	$^\circ\text{C/W}$
	Schottky			125	
Maximum Junction-to-Ambient ($t = \text{steady state}$) ^a	MOSFET		115		
	Schottky		130		

Notes

- a. Surface Mounted on FR4 Board.
- b. $t \leq 10$ sec.



MOSFET SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.6			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±12 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -20 V, V _{GS} = 0 V, T _J = 55 °C			-25	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ -5 V, V _{GS} = -4.5 V	-6			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = -4.5 V, I _D = -1.7 A		0.135	0.190	Ω
		V _{GS} = -3.0 V, I _D = -1.3 A		0.200	0.280	
Forward Transconductance ^a	g _{fs}	V _{DS} = -10 V, I _D = -1.7 A		4.0		S
Diode Forward Voltage ^a	V _{SD}	I _S = -1 A, V _{GS} = 0 V		-0.77	-1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = -3.5 V, V _{GS} = -4.5 V, I _D = -0.3 A		3.5	7.0	nC
Gate-Source Charge	Q _{gs}			0.85		
Gate-Drain Charge	Q _{gd}			0.60		
Turn-On Delay Time	t _{d(on)}	V _{DD} = -3.5 V, R _L = 11.5 Ω I _D ≅ -1 A, V _{GEN} = -4.5 V, R _G = 6 Ω		7	15	ns
Rise Time	t _r			10	20	
Turn-Off Delay Time	t _{d(off)}			11	20	
Fall Time	t _f			7	15	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = -1 A, di/dt = 100 A/μs		35	60	

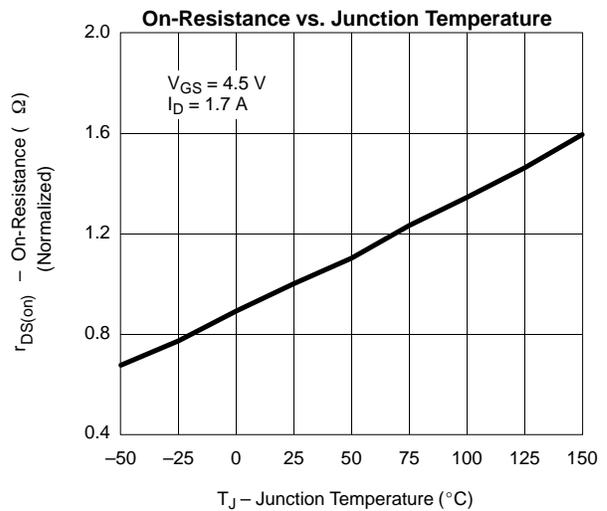
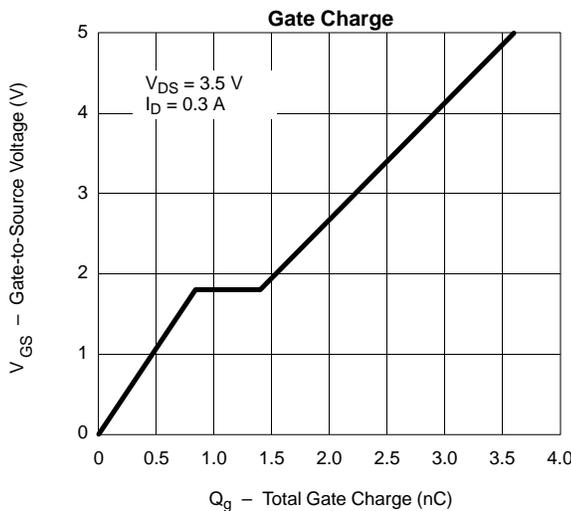
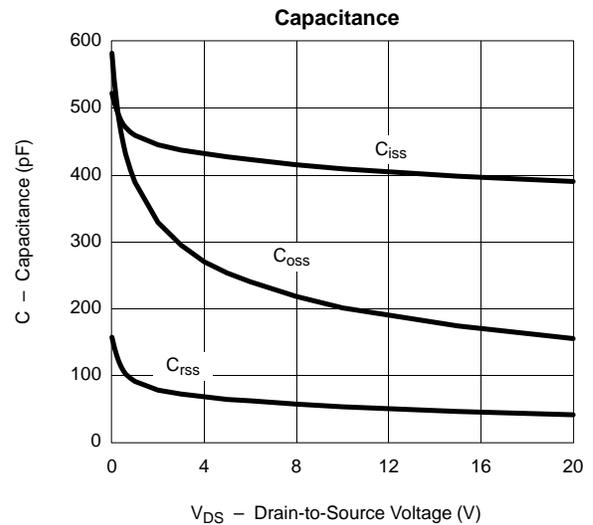
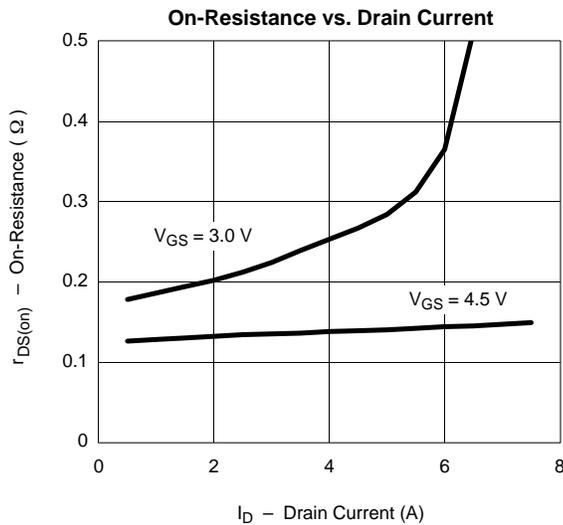
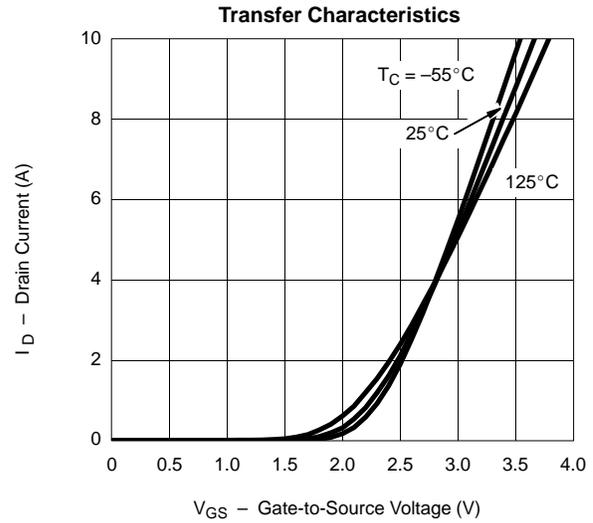
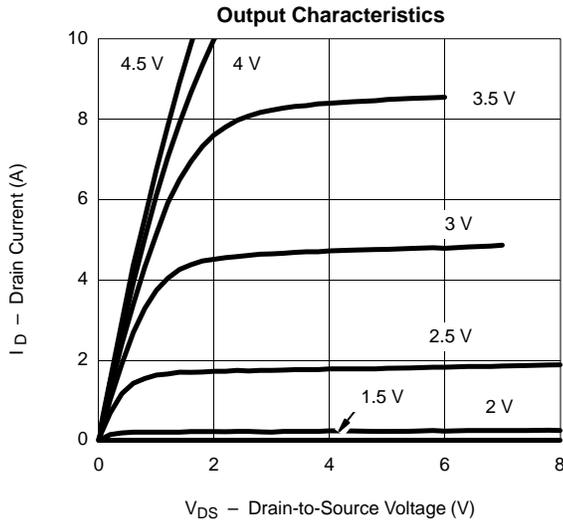
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

SCHOTTKY SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage Drop	V _F	I _F = 1 A		0.45	0.5	V
		I _F = 1 A, T _J = 125 °C		0.36	0.42	
Maximum Reverse Leakage Current	I _{rm}	V _r = 20 V		0.003	0.100	mA
		V _r = 20 V, T _J = 75 °C		0.1	1	
		V _r = 20 V, T _J = 125 °C		2	10	
Junction Capacitance	C _T	V _r = 10 V		62		pF

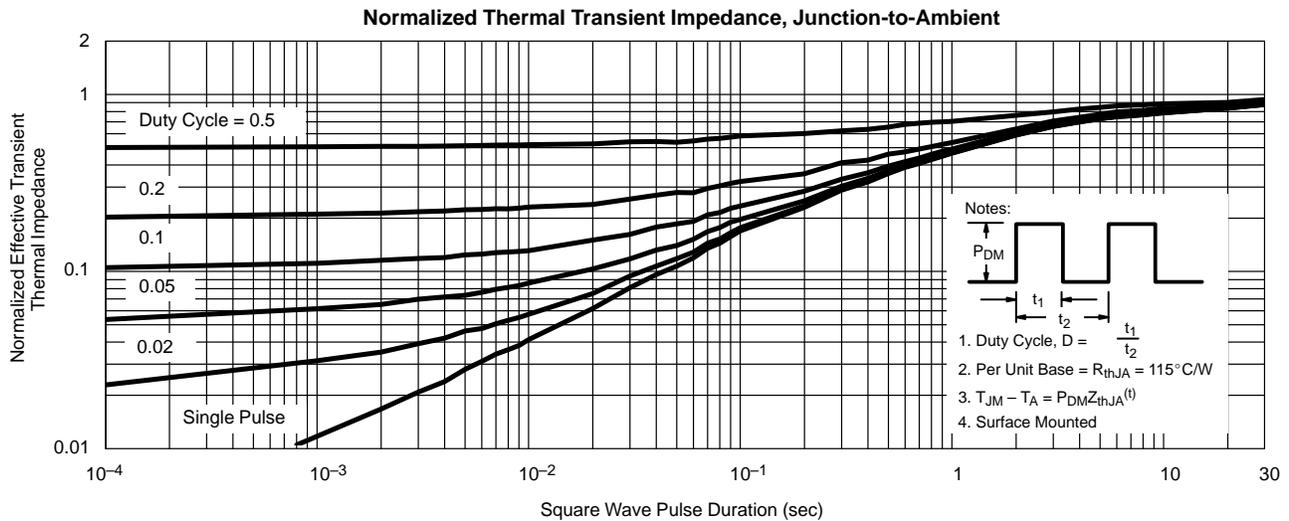
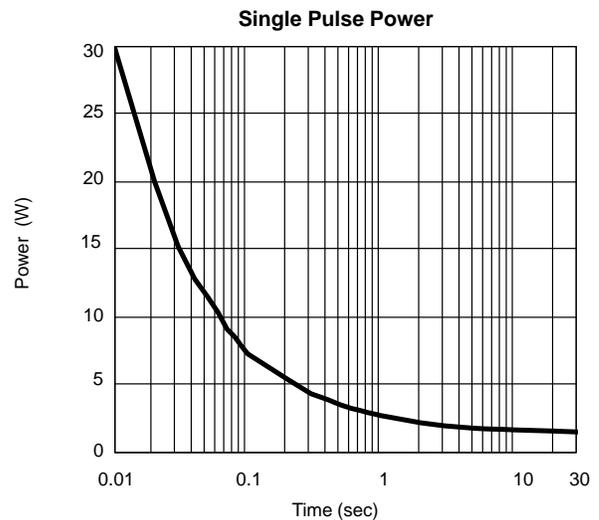
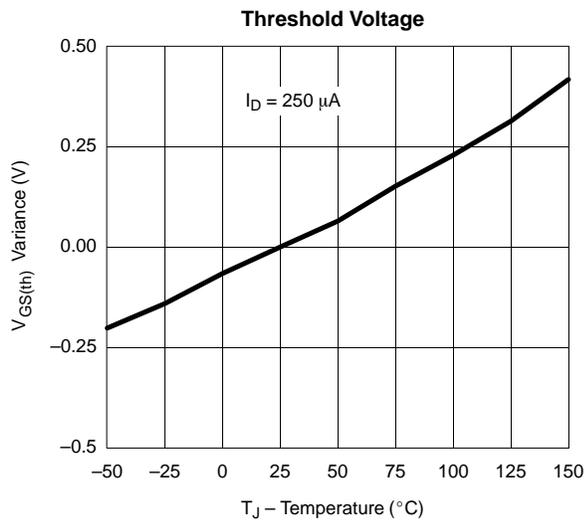
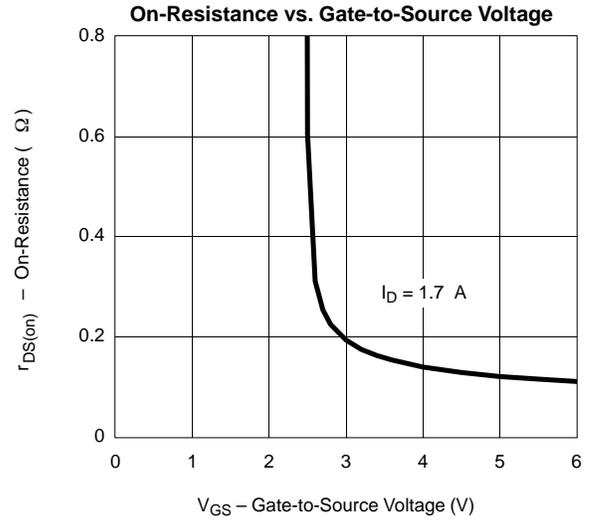
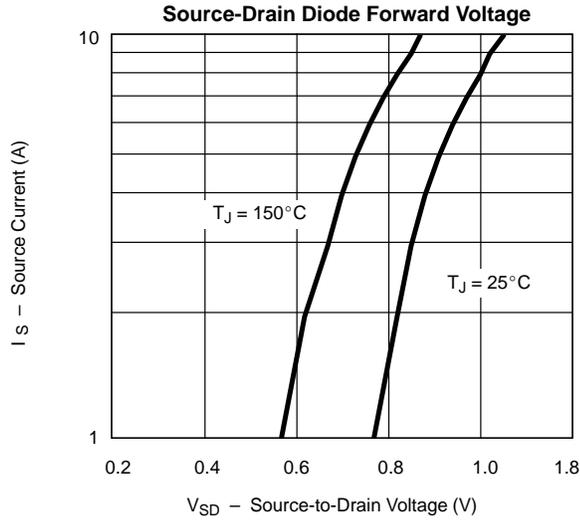


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) MOSFET





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SCHOTTKY

